

Silicon NPN Power Transistors

2SC2260

DESCRIPTION

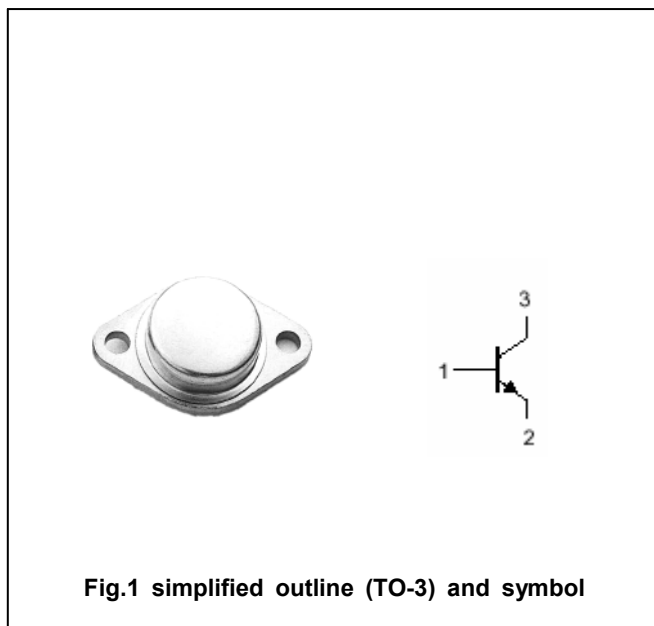
- With TO-3 package
- Complement to type 2SA980

APPLICATIONS

- For power switching and general purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings($T_a = \square$)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	160	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		8	A
I_B	Base current		3	A
P_C	Collector power dissipation	$T_C = 25 \square$	80	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-65~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA ; I_B=0$	100			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	6			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=3A ; I_B=0.3A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=160V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=3A ; V_{CE}=4V$	30		180	
f_T	Transition frequency	$I_C=0.5A ; V_{CE}=12V$		15		MHz

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PACKAGE OUTLINE

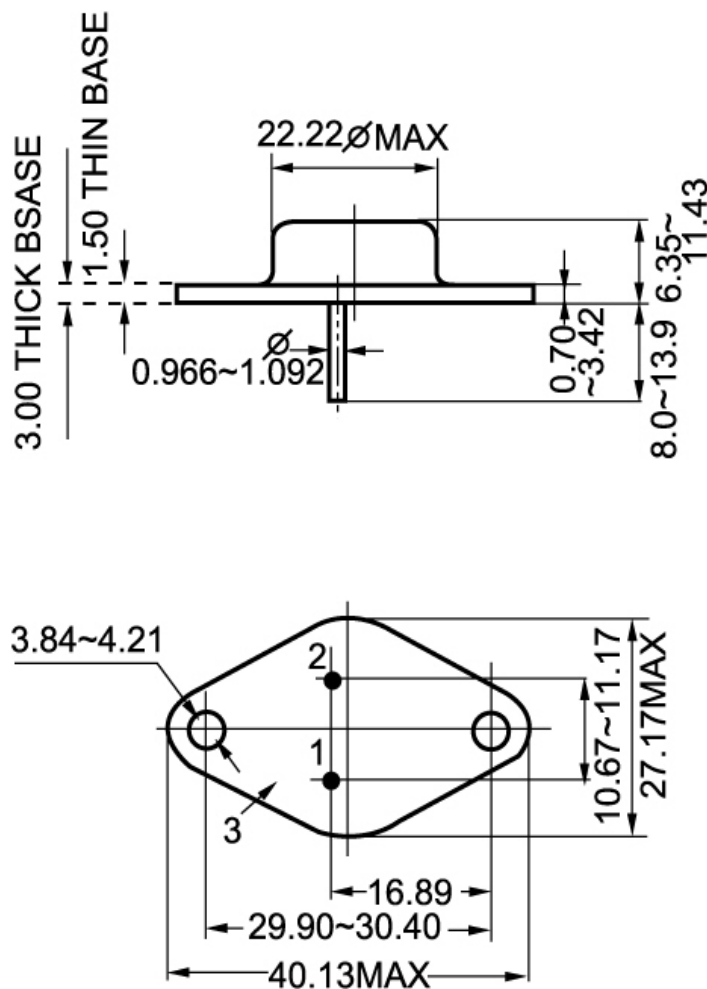


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)